AW318A Datasheet

Zhuhai Jieli Technology Co.,LTD

Version 1.2

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Revision History

Date	Revision	Description
2024.04.12	V1.0	Initial Release
2024.07.04	V1.1	Update IC Marking Information
2025.01.17	V1.2	Update Feature_Bluetooth





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AW318A Features

SYSTEM

- > 32bit CPU 160MHz
- ➤ Support MATH/AES128
- I-cache
- Support EMU
- On-chip SRAM 32kbyte
- Support MPU
- Support UDMA
- Built-In Flash
- ➤ 24MHz crystal oscillator
- > Internal low jitter low power RC oscillator
- Internal PLL

Bluetooth

- BLE6.0 +2.4GHz-Proprietary (DN Q334307)
- Support AoA Transmitter
- Support long range BLE
- Maximum transmitting power 8dBm
- Receiver sensitivity
 - ◆ -92dBm @BLE-1Mbps
 - ❖ -89dBm @BLE-2Mbps

Peripherals

- 1 x Full speed USB
- 4 x Multi-function 32bit timer
- ➤ 1 x IR RX/TX
- ➤ 1 x UART interface
- 1 x I²C Master/Slave interface
- 2 x SPI Master/Slave interface
- ➤ 1 x QDEC
- ➢ 3 x MCPWM
- ➤ 2 x LEDC
- 1 x 10bit ADC(3 Channel)
- 2 x GPIO Support function remapping

PMU

- Support temperature sensor
- ➤ VPWR range 2.7V to 5.5V
- ➢ IOVDD range 1.8V to 3.6V
- > Deep sleep mode (IOVDD @3.0V)
 - 170nA (External wakeup)
 - 1.37uA (32kHz RC OSC+wakeup)
 - 2.9uA (32kHz RC OSC+wakeup+16k retention SRAM)

Packages

➤ SOP8

Temperature

- Operating temperature
 - TC = -20° C to $+85^{\circ}$ C (standard range)
 - TC = -40° C to $+105^{\circ}$ C (extended range)
- Storage temperature -65℃ to +150℃

Applications

- Mouse devices
- Non-audio remote controller
- Selfie stick
- Page turner
- Adaptive USB
- Bluetooth moudle
- Price tag and other diversified IOT product



1 Block Diagram

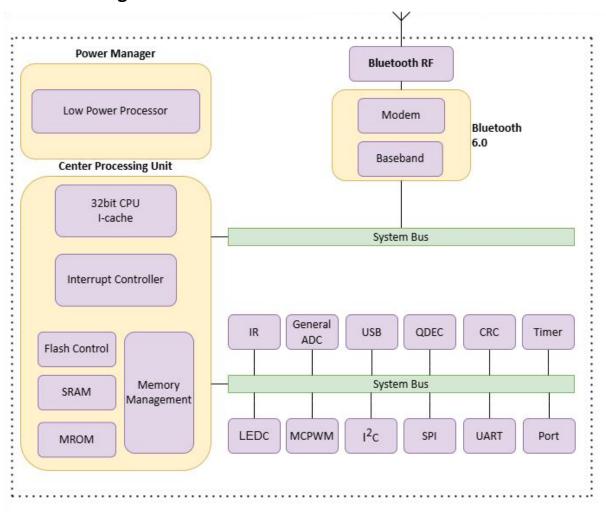


Figure 1-1 AW318A Block Diagram

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2 Pin Definition

2.1 Pin Assignment

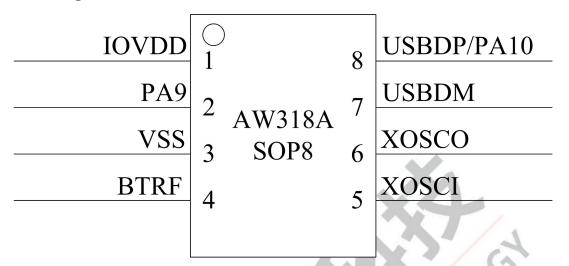


Figure 2-1 AW318A Pin Assignment

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2.2 Pin Description

Table 2-2-1 AW318A Pin Description

Pin No.	Name	Туре	IO Initial State	Description
1	IOVDD	Р		IO Power
2	PA9	1/0	Z	LVD(External Low Voltage Detection Input) ADC9(ADC Input Channel 9) SPIO_DAT3B
3	VSS	G		Ground
4	BTRF	RF		Bluetooth RF Antenna
5	XOSCI	I		Crystal Oscillator Input
6	xosco	0		Crystal Oscillator Output
7	USBDM	1/0	15kΩ Pull-down	ADC13(ADC Input Channel 13)
8	USBDP	1/0	15kΩ Pull-down	ADC14(ADC Input Channel 14)
°	PA10	1/0	Z	ADC10(ADC Input Channel 10)

Note

- 1.IO initial state abbreviations Z--High resistance, H--High level, L--Low level, X--May be changed during power on.
- 2.Timer, IR,MCPWM, QDEC, UART, LEDC, I²C, SPI1 functions can be remapped to any I/O.

Table 2-2-2 Pin Types Description

Pin Type	Description	Pin Type	Description
Р	Power	1/0	Input or Output
G	Ground	I .	Input
RF	RF antenna	0	Output



3 Electrical Characteristics

3.1 Absolute Maximum Ratings

Table 3-1 Absolute Maximum Ratings

Symbol	Parameter	Min	Max	Unit
Topt	Operating temperature	-20	+85	${\mathbb C}$
Tstg	Storage temperature	-65	+150	$^{\circ}$
IOVDD		-0.3	3.6	V
GPIO	Input voltage of GPIO (except PA7)	-0.3	3.6	V

Note

1.Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device.

3.2 ESD Ratings

Table 3-2 ESD Ratings

Parameter	Тур	Test pin	Reference standard
Human Body Mode	±8kV	All pins	JEDEC EIA/JESD22-A114
Machine Mode	±400V	All pins	JEDEC EIA/JESD22-A115
Charge Device Model	±2kV	All pins	ANSI/ESDA/JEDEC JS-002-2022

3.3 PMU Characteristics

Table 3-3-1 PMU Characteristics under IOVDD supply

Symbol	Parameter	Conditions		Тур	Max	Unit
IOVDD	Power supply	-	1.8	-	3.6	V

3.4 IO Characteristics

Table 3-4 IO Characteristics

Input Char	Input Characteristics							
Symbol	Parameter	Conditions	10	Min	Max	Unit		
V _{IL}	Low-Level Input Voltage	IOVDD = 3.0V	PA9,PA10	-0.3	1.4	V		
V _{IH}	High-Level Input Voltage	IOVDD = 3.0V	PA9,PA10 USBDP USBDM	1.7	3.3	V		
Output Cha	aracteristics							
Symbol	Parameter	Conditions	10	Ty	ур	Unit		
I _{OL}	Output Current	IOVDD = 3.0V Voutput = 0.3V	PA9,PA10	9(HI	D=0) D=1) ID=2)	mA		



				54(HD=3)	
		IOVDD = 3.0V	USBDP	8	^
		Voutput = 0.3V	USBDM	8	mA
				3(HD=0)	
		IOVDD = 3.0V	PA9,PA10	9(HD=1)	mA
	Outrast Commant	Voutput = 2.7V	PA9,PA10	21(HD=2)	MA
I _{OH}	Output Current			54(HD=3)	
		IOVDD = 3.0V	USBDP	0	^
		Voutput = 2.7V	USBDM	8	mA
Internal Re	esistance Characteristics				
Symbol	Parameter	Conditions	10	Тур	Unit
				10k(PU=1)	
	Pull-up Resistance	IOVDD = 3.0V	PA9,PA10	100k(PU=2)	Ω
R_{pu}				1M(PU=3)	
		IOVDD = 3.0V	USBDP	1.5k	Ω
		IOVDD = 3.0V	USBDM	180k	Ω
				10k(PD=1)	
		IOVDD = 3.0V	PA9,PA10	100k(PD=2)	Ω
R _{pd}	Pull-down Resistance			1M(PD=3)	
		10//00 - 3 0//	USBDP	15k	0
		IOVDD = 3.0V	USBDM	TOK	Ω

Note

3.5 BT Characteristics

3.5.1 Transmitter

Table 3-5-1 Transmitter characteristics

Parameter	Conditions	Min	Тур	Max	Unit
Maximum RF Transmit Power	BLE-1Mbps		7	8	dBm

3.5.2 Receiver

Table 3-5-2 Receiver characteristics

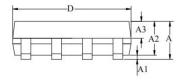
Parameter	Conditions	Min	Тур	Max	Unit
	BLE-1Mbps		-92		dBm
Concitivity	BLE-2Mbps		-89		dBm
Sensitivity	BLE-S2		-95		dBm
	BLE-S8		-100		dBm

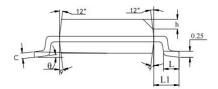
^{1.}Internal pull-up/pull-down resistance accuracy ±20%.

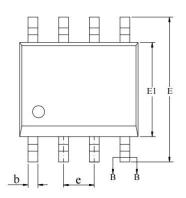


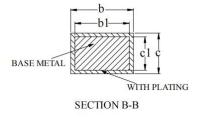
4 Package Information

4.1 SOP8









MILLIMETER SYMBOL NOM MAX MIN A 1.75 0.225 A1 0.10 1.30 1.50 A2 0.70 A3 0.60 0.39 0.47 b bl 0.38 0.44 0.41 0.20 0.24 0.19 0.20 0.21 c1 D 4.80 5.00 E 5.80 6.20 El 3.80 3.90 4.00 e 1.27BSC 0.50 h 0.25 0.50 0.80 L Ll 8° θ 0

Figure 4-1 AW318A Package



5 IC Marking Information

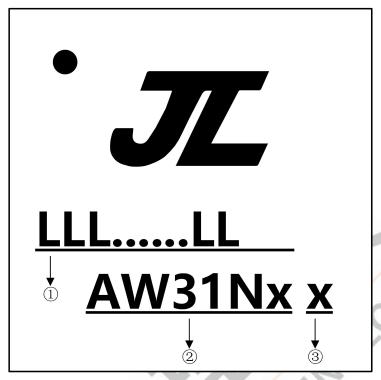


Figure 5-1 AW318A Package Outline

- 1 LLL.....LL LOT No. , It contains 7 to 18 alphanumerics
- 2 AW31Nx Chip Model
- 3 x Built-in flash size
 - 0 No Flash Memory
 - 2 2Mbit Flash
 - 4 4Mbit Flash



6 Solder-Reflow Condition

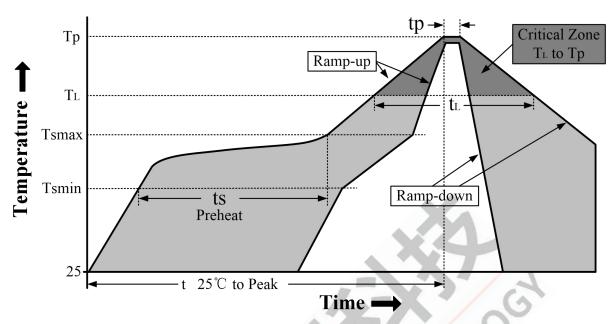


Figure 6-1 Classification Reflow Profile

Table 6-1 Classification Profiles

	Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly	
	Temperature Min (T _{smin})	100℃	150℃	
Preheat/Soak	Temperature Max (T _{smax})	150°C	200℃	
	Time (ts) from (T _{smin} to T _{smax})	60-120 seconds	60-180 seconds	
Average ramp-	up rate (T _{smax} to T _p)	3℃/second max	3℃/second max	
Liquidus temperature (T _L)		183℃	217℃	
Time (t _L) maint	ained above T _L	60-150 seconds	60-150 seconds	
Peak package b	ood <mark>y temperature (T_p)</mark>	See Table 6-2	See Table 6-3	
Time within 5°0	C of actual	10-30 seconds	20-40 seconds	
Peak Temperature (tp) ²		10-30 Seconds	20-40 seconds	
Ramp-down rate (Tp to TL)		6°C/second max	6°C/second max	
Time 25℃ to p	eak temperature	6 minutes max	8 minutes max	

Note

- 1.All temperatures refer to topside of the package, measured on the package body surface
- 2.Time within 5 $^{\circ}$ C of actual peak temperature (tp) specified for the reflow profiles is a "supplier" and "user" maximum.

Table 6-2 SnPb Classification Temperature

Package	Volume mm ³	Volume mm³
Thickness	< 350	≥ 350
<2.5 mm	240 +0/-5℃	225 +0/-5°C
≥2.5 mm	225 +0/-5℃	225 +0/-5°C



Table 6-3 Pb-free - Classification Temperature

Package Thickness	Volume mm³ < 350	Volume mm ³ 350 - 2000	Volume mm³ > 2000
< 1.6mm	260℃	260℃	260℃
1.6 mm - 2.5mm	260℃	250℃	245℃
> 2.5mm	250℃	245℃	245℃

Note

1.*Tolerance The device manufacturer/supplier shall assure process compatibility up to and including the stated classification temperature (this means Peak reflow temperature +0 $^{\circ}$ C.For example 260 $^{\circ}$ C+0 $^{\circ}$ C)at the rated MSL level.

